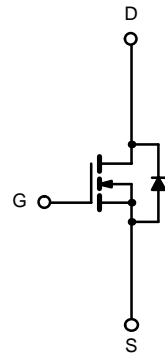
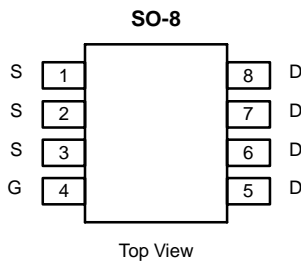




N-Channel 80-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
80	0.0165 @ $V_{GS} = 10$ V	9.5
	0.022 @ $V_{GS} = 6.0$ V	8.3

TrenchFET[®]
Power MOSFETs



Ordering Information: Si4896DY
Si4896DY-T1 (with Tape and Reel)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	80		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	$T_A = 25^\circ\text{C}$	I_D	9.5	6.7	A
	$T_A = 70^\circ\text{C}$		7.6	5.4	
Pulsed Drain Current		I_{DM}	50		
Avalanch Current		I_{AS}	40		
Continuous Source Current (Diode Conduction) ^a		I_S	2.8	1.4	
Maximum Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	3.1	1.56	W
	$T_A = 70^\circ\text{C}$		2.0	1.0	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		$^\circ\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	33	40	$^\circ\text{C}/\text{W}$
	Steady State		65	80	
Maximum Junction-to-Foot (Drain)		R_{thJF}	17	21	

Notes

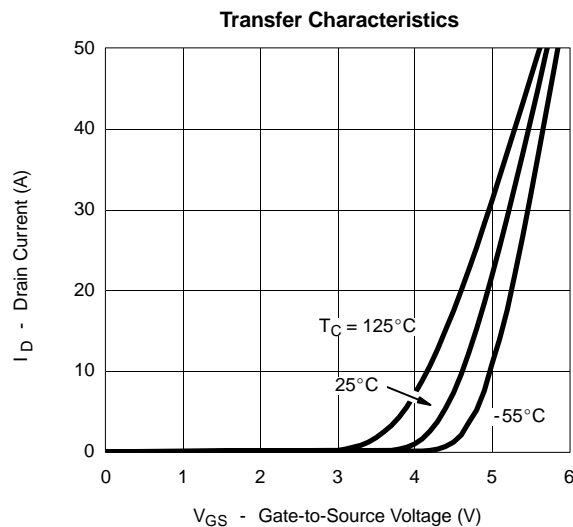
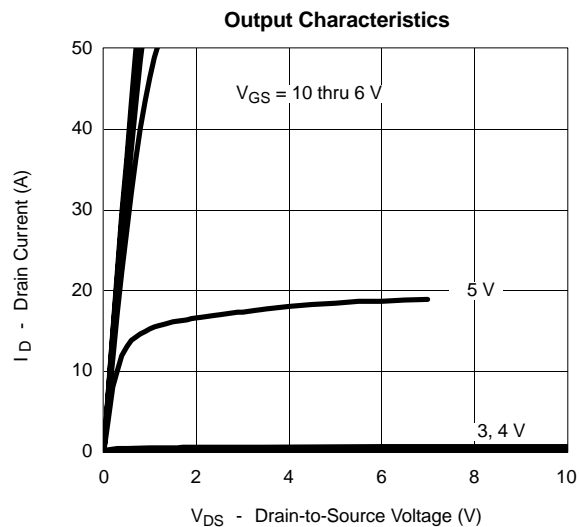
a. Surface Mounted on 1" x 1" FR4 Board.

SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.0			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 64 V, V _{GS} = 0 V			1	μA
		V _{DS} = 64 V, V _{GS} = 0 V, T _J = 55 °C			5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	50			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 10 A		0.0135	0.0165	Ω
		V _{GS} = 6.0 V, I _D = 8.0 A		0.0175	0.022	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 10 A		25		S
Diode Forward Voltage ^a	V _{SD}	I _S = 2.8 A, V _{GS} = 0 V		0.75	1.1	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = 40 V, V _{GS} = 10 V, I _D = 10 A		34	41	nC
Gate-Source Charge	Q _{gs}			7.5		
Gate-Drain Charge	Q _{gd}			11.0		
Gate Resistance	R _g		0.2	0.85	1.2	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 40 V, R _L = 40 Ω I _D ≅ 1.0 A, V _{GEN} = 10 V, R _G = 6 Ω		17	25	ns
Rise Time	t _r			11	17	
Turn-Off Delay Time	t _{d(off)}			40	60	
Fall Time	t _f			31	45	
Source-Drain Reverse Recovery Time	t _{rr}		I _F = 2.8 A, di/dt = 100 A/μs		45	

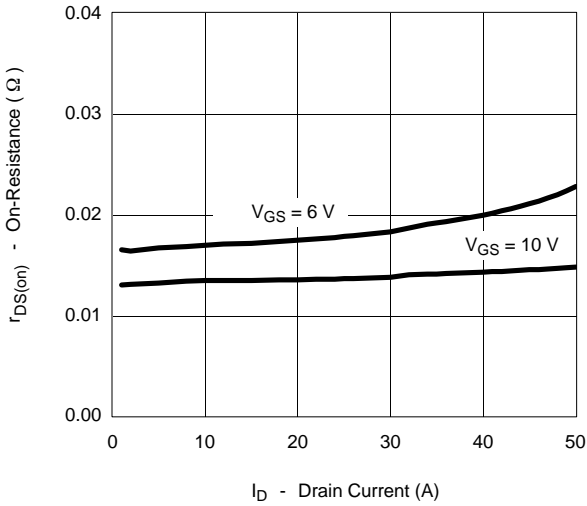
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

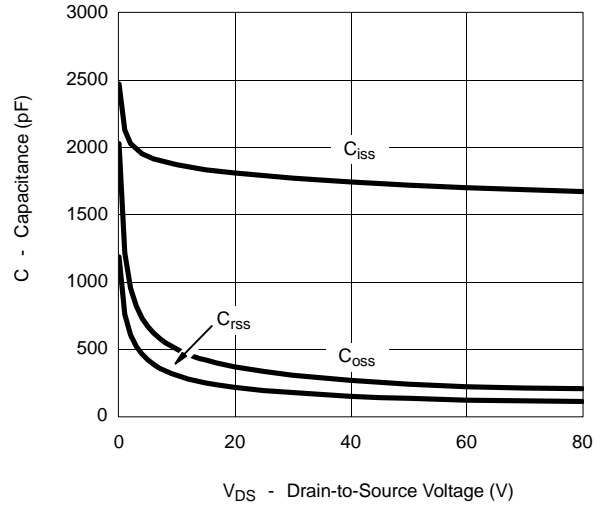
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

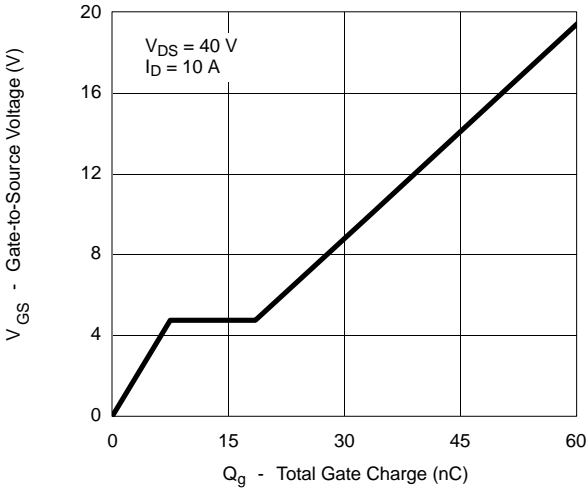
On-Resistance vs. Drain Current



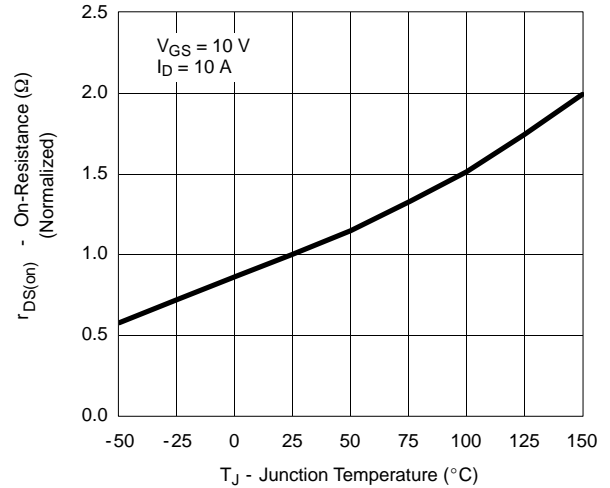
Capacitance



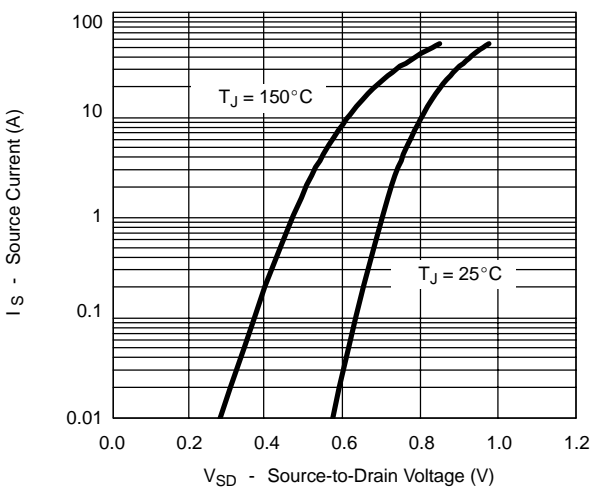
Gate Charge



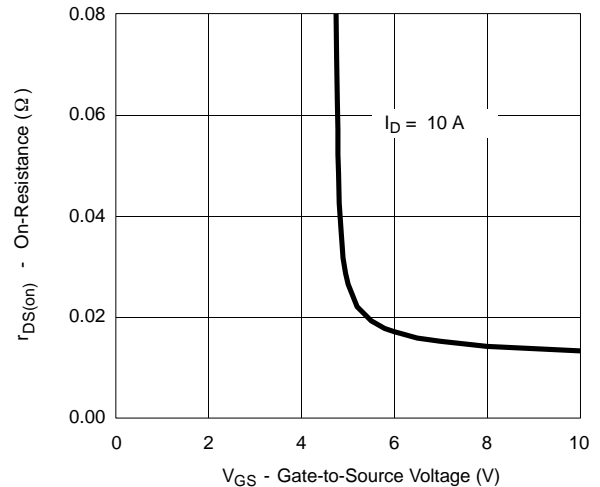
On-Resistance vs. Junction Temperature



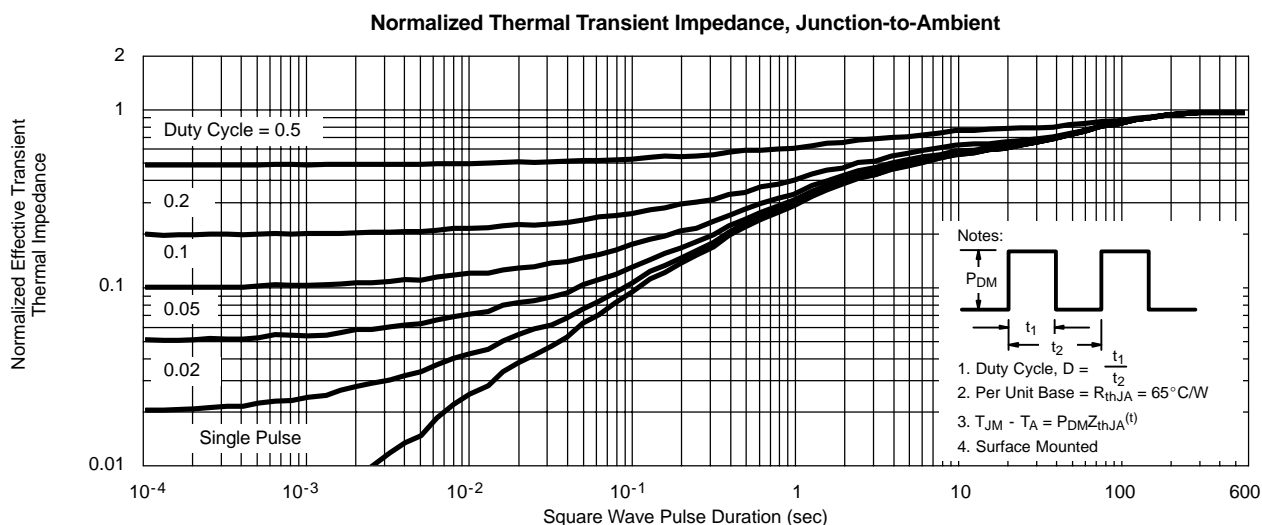
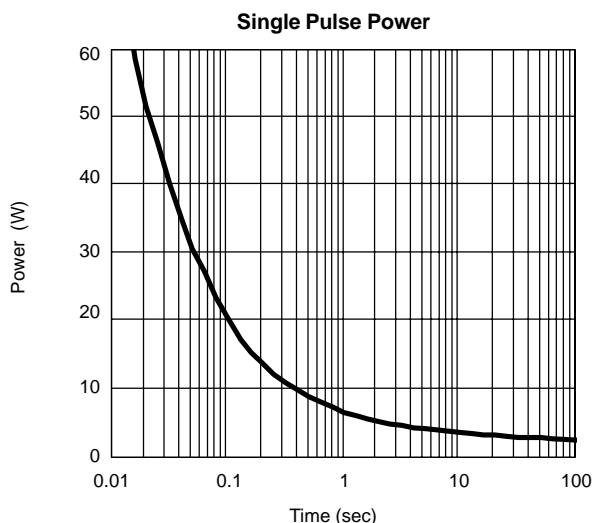
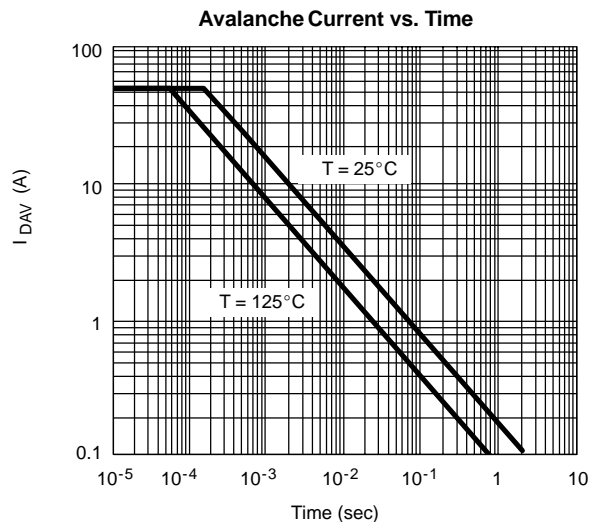
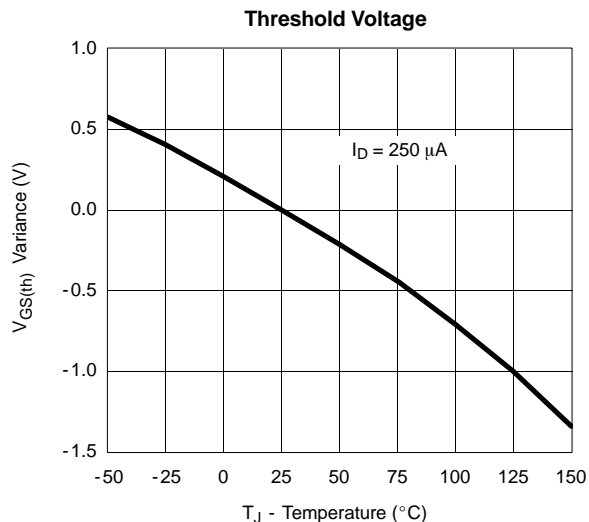
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

